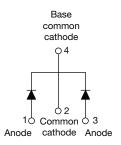


HEXFRED®, Ultrafast Soft Recovery Diode, 2 x 4 A



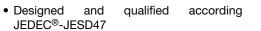
3L TO-220AB



PRIMARY CHARACTERISTICS								
Package 3L TO-220AB								
I _{F(AV)}	2 x 4 A							
V_{R}	600 V							
V _F at I _F	1.4 V							
t _{rr} typ.	17 ns							
T _J max.	150 °C							
Circuit configuration	Common cathode							

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}





 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA08TA60C... is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A per leg continuous current, the VS-HFA08TA60C... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TA60C... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V_{R}		600	V					
Maximum continuous forward current per leg	_	T _C = 100 °C	4						
per device	I _F		8	^					
Single pulse forward current	I _{FSM}		25	Α					
Maximum repetitive forward current	I _{FRM}		16						
Maximum nawar dissination	D	T _C = 25 °C	25	W					
Maximum power dissipation	P_{D}	T _C = 100 °C	10	VV					
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C					



ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	600	-	-				
Maximum forward voltage		I _F = 4.0 A		-	1.5	1.8	V		
	V _{FM}	I _F = 8.0 A	See fig. 1	-	1.8	2.2			
		I _F = 4.0 A, T _J = 125 °C]	-	1.4	1.7			
Maximum reverse	l	V _R = V _R rated	See fig. 2	-	0.17	3.0	μA		
leakage current	I _{RM}	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See lig. 2	-	44	300	μΑ		
Junction capacitance	C _T	$V_R = 200 \text{ V}$ See fig. 3		ı	4.0	8.0	pF		
Series inductance	L _S	Measured lead to lead 5 mm from p	-	8.0	-	nΗ			

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	A/μs, V _R = 30 V	-	17	-			
Reverse recovery time See fig. 5, 6 and 16	t _{rr1}	T _J = 25 °C		-	28	42	ns		
ocong. o, o and ro	t _{rr2}	T _J = 125 °C	$I_F = 4.0 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	38	57			
Peak recovery current	I _{RRM1}	$T_J = 25 ^{\circ}C$		-	2.9	5.2	- A - nC		
See fig. 7 and 8	I _{RRM2}	T _J = 125 °C		-	3.7	6.7			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	40	60			
See fig. 9 and 10	Q _{rr2}	T _J = 125 °C		-	70	105			
Peak rate of fall of recovery	dI _{(rec)M} /dt1	T _J = 25 °C		-	280	-			
current during t _b See fig. 11 and 12	dI _{(rec)M} /dt2	T _J = 125 °C		-	235	-	A/µs		

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	5.0					
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-					
Weight			-	2.0	-	g				
vveigni			-	0.07	-	OZ.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style 3L TO-220AB	HFA08TA60C							

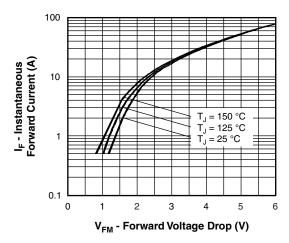


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

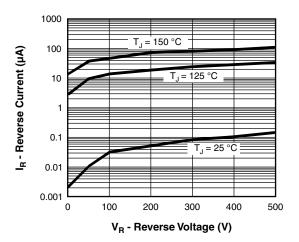


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

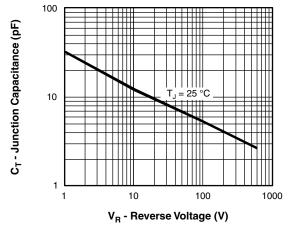


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

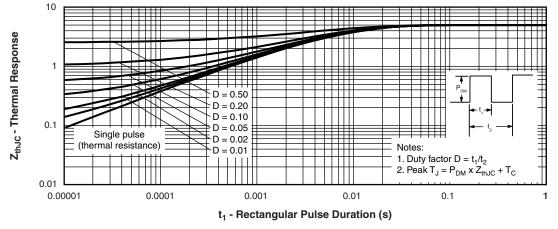


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

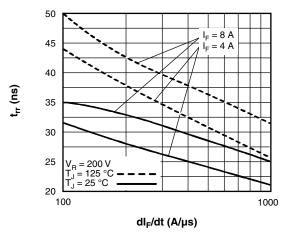


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

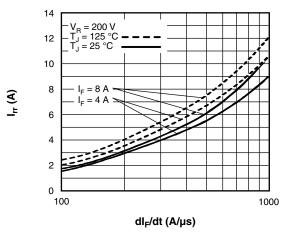


Fig. 6 - Typical Recovery Current vs. dI_F/dt

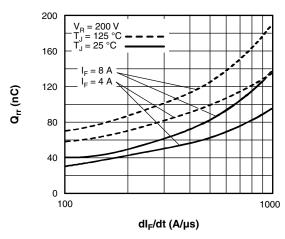


Fig. 7 - Typical Stored Charge vs. dl_F/dt

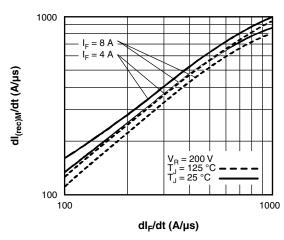
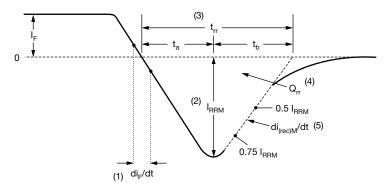


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

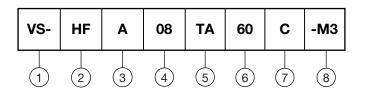
(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

Electron irradiated

Current rating (08 = 8 A)

5 - Package:

TA = 3L TO-220AB

6 - Voltage rating (60 = 600 V)

- Circuit configuration:

C = common cathode

7 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

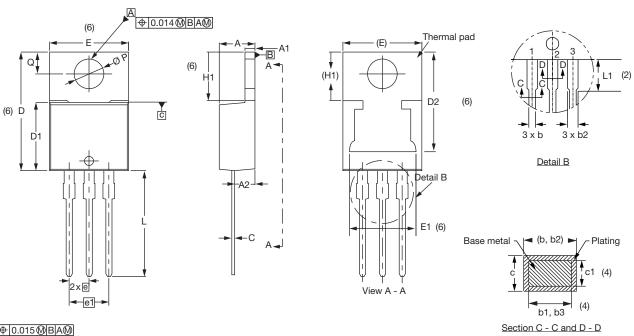
ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA08TA60C-M3	50	1000	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS								
Dimensions	www.vishay.com/doc?96154							
Part marking information	www.vishay.com/doc?95028							

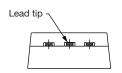


3L TO-220AB

DIMENSIONS in millimeters and inches



⊕ 0.015 **M** B A **M**



Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIM	IETERS	INCHES		NOTES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183			D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055			E	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355		1		•			•	

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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Vishay

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